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SILICON N-CHANNEL JUNCTION FIELD-EFFECT TRANSISTOR

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	Vdc
Drain-Gate Voltage	V_{DG}	30	Vdc
Gate-Source Voltage	V_{GS}	-30	Vdc
Gate Current	I_G	10	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.0	mW mW/ $^\circ\text{C}$
Operating Junction Temperature	T_J	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +200	$^\circ\text{C}$

*ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate-Source Breakdown Voltage ($I_G = -1.0 \mu\text{Adc}, V_{DS} = 0$)	$V_{(BR)GSS}$	-30	—	Vdc
Gate Reverse Current ($V_{GS} = -20 \text{ Vdc}, V_{DS} = 0$) ($V_{GS} = -20 \text{ Vdc}, V_{DS} = 0, T_A = 150^\circ\text{C}$)	I_{GSS}	—	-0.5 -500	nAdc
Gate-Source Cutoff Voltage ($I_D = 0.5 \text{ nAdc}, V_{DS} = 15 \text{ Vdc}$)	$V_{GS(off)}$	—	-8.0	Vdc
Gate-Source Voltage ($I_D = 0.4 \text{ mAdc}, V_{DS} = 15 \text{ Vdc}$)	V_{GS}	-1.0	-7.5	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current (1) ($V_{DS} = 15 \text{ Vdc}, V_{GS} = 0$)	I_{DSS}	4.0	20	mAdc

Forward Transfer Admittance ($V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ kHz}$) (1) ($V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 200 \text{ MHz}$)	$ V_{fs} $	3500 3200	6500	μhos
Input Conductance ($V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 200 \text{ MHz}$)	$R_{(y_{ig})}$	—	800	μhos
Output Conductance ($V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ kHz}$) (1) ($V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 200 \text{ MHz}$)	$ V_{os} $ $R_{(y_{og})}$	— —	35 200	μhos
Input Capacitance ($V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C_{iss}	—	6.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C_{rss}	—	2.0	pF
Common-Source Spot Noise Figure ($V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, R_S = 1000 \text{ ohms}, f = 100 \text{ MHz}$)	NF	—	2.5	dB

*Indicates JEDEC Registered Data.

(1)Pulse Test: Pulse Width < 100 ms, Duty Cycle < 10%.

